

forming a dielectric cap on a top of the sidewalls of the conductive layer;  
removing the fill layer to expose an inside of the container structure; and  
removing at least a portion of the insulating layer to expose an outside of the container structure.

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118. (New) The method of claim 117, wherein removing at least a portion of the insulating layer to expose an outside of the container structure occurs subsequent to forming a dielectric cap on a top of the sidewalls of the conductive layer.

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119. (New) The method of claim 117, wherein forming a dielectric cap on a top of the sidewalls of the conductive layer further comprises:

forming a dielectric layer on the insulating layer, the conductive layer and the fill layer; and  
removing the dielectric layer from the insulating layer and the fill layer.

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120. (New) The method of claim 117, wherein removing the dielectric layer from the insulating layer and the fill layer further comprises removing the dielectric layer from the insulating layer and the fill layer using an anisotropic etch.

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121. (New) A method of forming a semiconductor structure, comprising:  
forming an insulating layer on a substrate, wherein the insulating layer comprises at least one insulating material selected from the group consisting of oxides, nitrides and borophosphosilicate glass;  
forming an opening in the insulating layer, wherein the opening has a bottom on an exposed portion of the substrate and sidewalls defined by the insulating layer;  
forming a conductive layer on the insulating layer and the exposed portion of the substrate, wherein the conductive layer comprises at least one silicon material selected from the group consisting of amorphous silicon, polysilicon and hemispherical grain polysilicon;